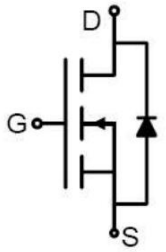
# APG048N03G

**N-Channel Enhancement Mosfet**

**DATA SHEET**

## Features

- 30V,58A
  $R_{DS(ON)}$ <4.8mΩ @$V_{GS}$=10V TYP:4.3mΩ
  $R_{DS(ON)}$ <8.5mΩ @$V_{GS}$=4.5V TYP:6.5mΩ
- Split Gate Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge




**Schematic Diagram**

## Applications

- Power management
- DC/DC converters




**Marking and pin Assignment**

## Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity (PCS) |
|---|---|---|---|---|---|
| G048N03G | APG048N03G | PDFN5X6 | - | - | 5000 |

## ABSOLUTE MAXIMUM RATINGS ($T_J$=25℃ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 30 | V |
| Gate-Source Voltage | $V_{GS}$ | ±20 | V |
| Continuous Drain Current (Tc=25℃) (1) | $I_D$ | 58 | A |
| Continuous Drain Current (Tc=100℃) | $I_D$ | 46 | A |
| Pulsed Drain Current (1) | $I_{DM}$ | 125 | A |
| Drain Power Dissipation | $P_D$ | 27 | W |
| Single Pulsed Avalanche Energy (2) | $E_{AS}$ | 48 | mJ |
| Thermal Resistance from Junction to Ambient (3) | $R_{\theta JA}$ | 60 | ℃/W |
| Thermal Resistance from Junction to Case | $R_{\theta JC}$ | 5.2 | ℃/W |
| Junction Temperature | $T_J$ | -55~ +150 | ℃ |
| Storage Temperature | $T_{STG}$ | -55~ +150 | ℃ |

**Notes:**

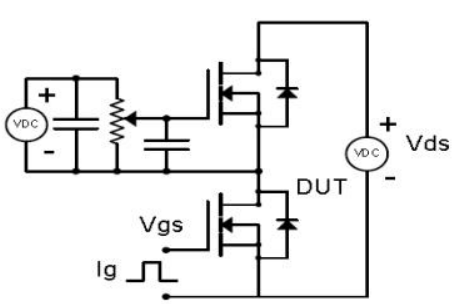
1) Repetitive Rating: pulse width limited by maximum junction temperature
2) EAS condition : $T_J$=25℃, $V_{DD}$=25V, $V_G$=10V, L=0.1mH, $R_g$=25Ω, $I_{AS}$=31A
3) The value of RθJA Mounted on FR4 Board（25.4mm*25.4mm*t1.6mm）With 2oz Copper TA=25℃

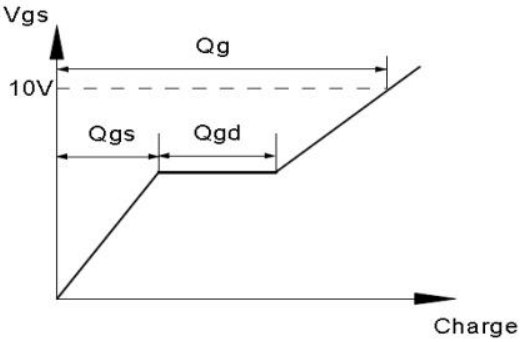
## MOSFET ELECTRICAL CHARACTERISTICS($T_J$=25℃ unless otherwise noted)

| Parameter | Symbol | Test Condition | Min | Type | Max | Unit |
|---|---|---|---|---|---|---|
| **Static Characteristics** | | | | | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0V, $I_D$ =250μA | 30 | - | - | V |
| Zero gate voltage drain current | $I_{DSS}$ | $V_{DS}$ =30V, $V_{GS}$ = 0V | - | - | 1 | μA |
| Gate-body leakage current | $I_{GSS}$ | $V_{GS}$ =±20V, $V_{DS}$ = 0V | - | - | ±100 | nA |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}$ =$V_{GS}$, $I_D$ =250μA | 1 | 1.7 | 2.5 | V |
| Drain-source on-resistance | $R_{DS(on)}$ | $V_{GS}$ =10V, $I_D$ =15A | - | 4.3 | 4.8 | mΩ |
| | | $V_{GS}$ =4.5V, $I_D$ =15A | - | 6.8 | 8.5 | mΩ |
| Forward transconductance | $R_g$ | $V_{GS}$= 0V, $V_{DS}$= 0V, f=1.0MHz | - | 1.8 | - | Ω |
| **Dynamic characteristics** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$ =15V, VGS=0V, f=1MHz | - | 882 | - | pF |
| Output Capacitance | $C_{oss}$ | | - | 380 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 65 | - | |
| **Switching characteristics** | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}$=15V, $I_D$=15A, $R_G$=3.3Ω, $V_{GS}$=10V | - | 7 | - | nS |
| Turn-on rise time | $t_r$ | | - | 42 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 16 | - | |
| Turn-off fall time | $t_f$ | | - | 6.2 | - | |
| Total Gate Charge | Qg | $V_{DS}$=15V, $I_D$=15A, $V_{GS}$=10V | - | 16.5 | - | nC |
| Gate-Source Charge | Qgs | | - | 2.9 | - | |
| Gate-Drain Charge | Qgd | | - | 3.5 | - | |
| **Source-Drain Diode characteristics** | | | | | | |
| Diode Forward voltage | $V_{SD}$ | $T_J$=25℃, $V_{GS}$ =0V, $I_S$=15A | - | 0.8 | 1.2 | V |
| Diode Forward current | $I_S$ | $T_C$=25℃ | - | - | 58 | A |

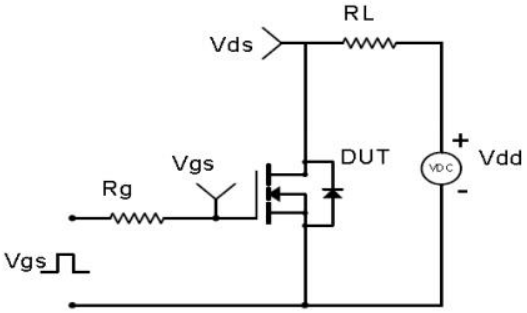
## Test Circuit & Waveform

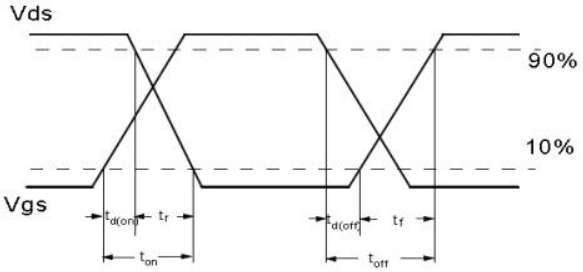
Gate Charge Test Circuit & Waveform



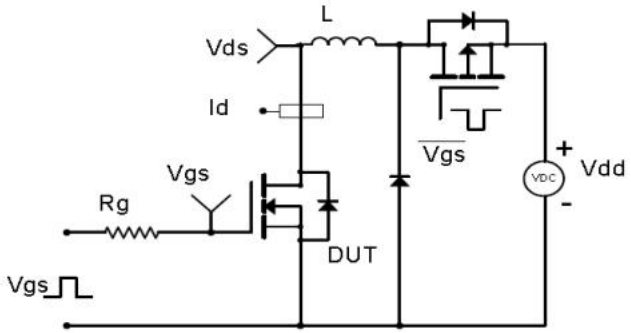



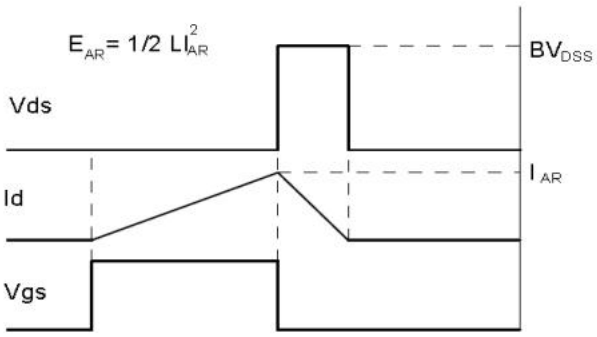

Resistive Switching Test Circuit & Waveforms



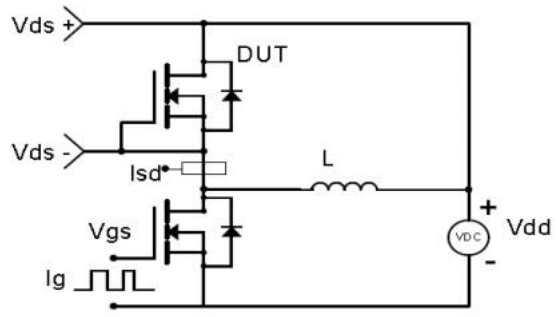



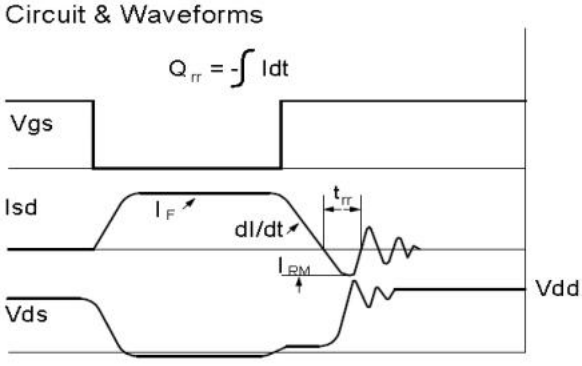

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms




Diode Recovery Test Circuit & Waveforms



# Typical Characteristics

**Figure 1. Output Characteristics**

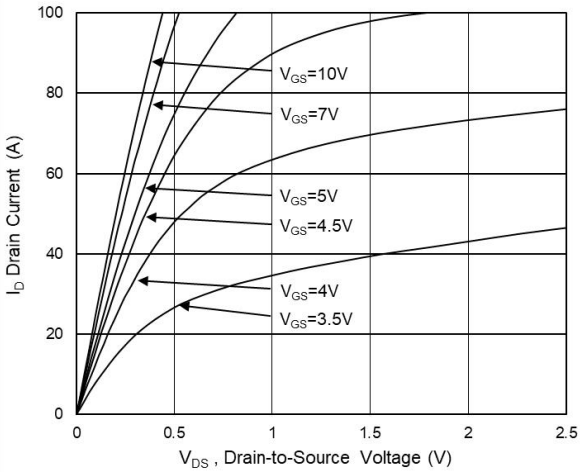



**Figure 2. On-Resistance vs G-S Voltage**

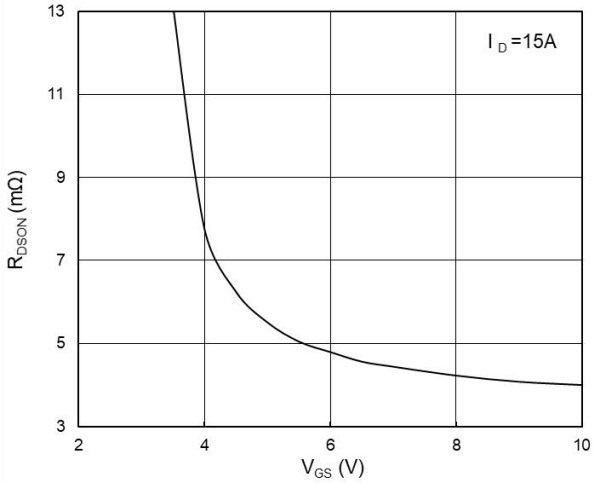



**Figure 3. Source Drain Forward Characteristics**

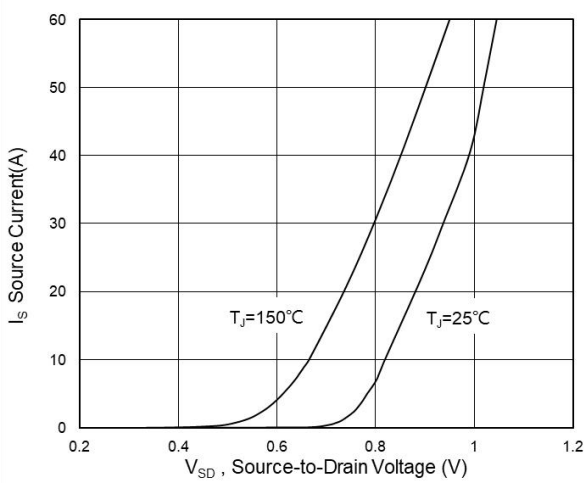



**Figure 4. Gate-Charge Characteristics**

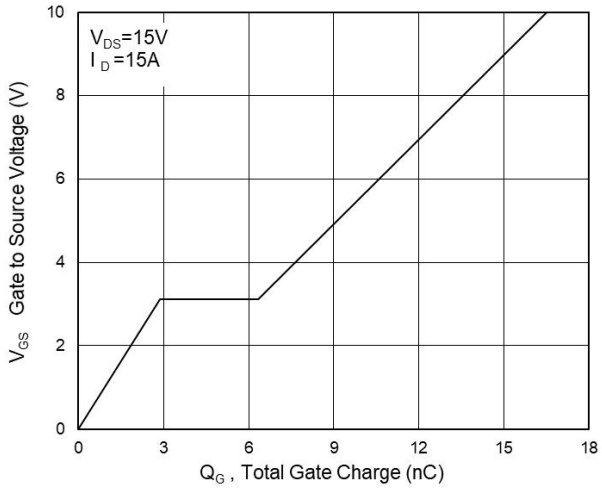



**Figure 5. $V_{th}$ vs Junction Temperature**

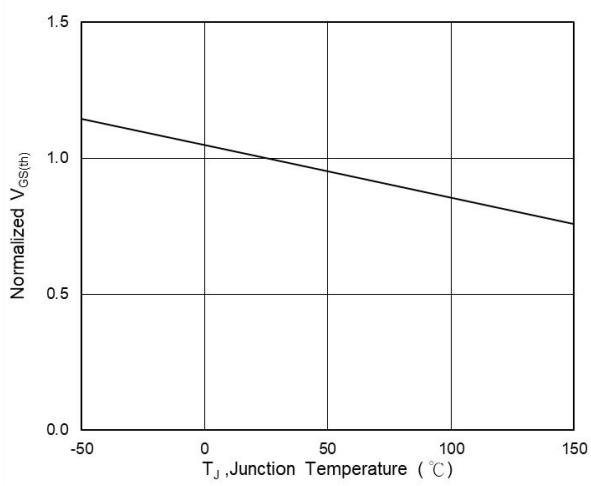
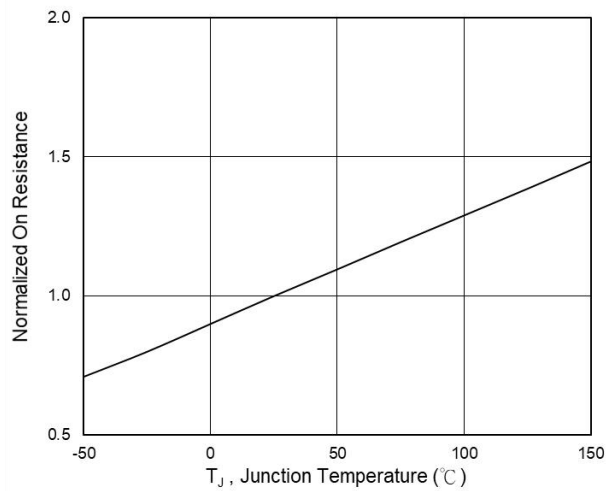



**Figure 6. $R_{DS(ON)}$ vs Junction Temperature**



# Typical Characteristics

**Figure 7. Capacitance**

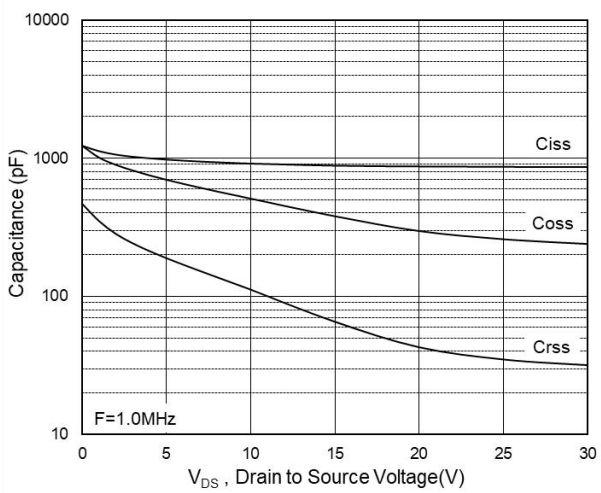



**Figure 8. Safe Operating Area**

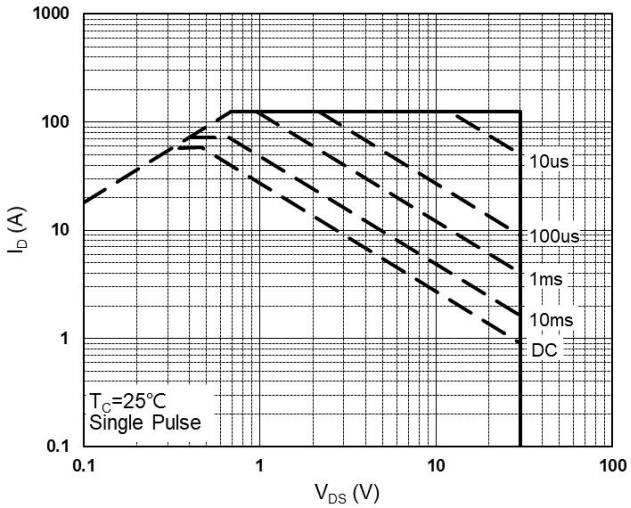
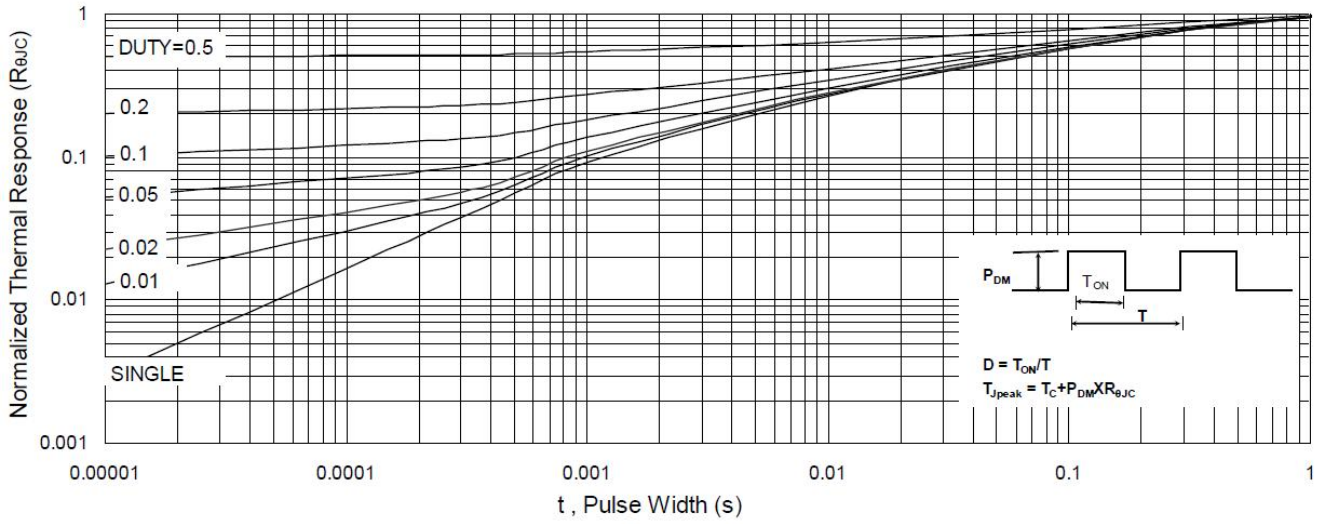
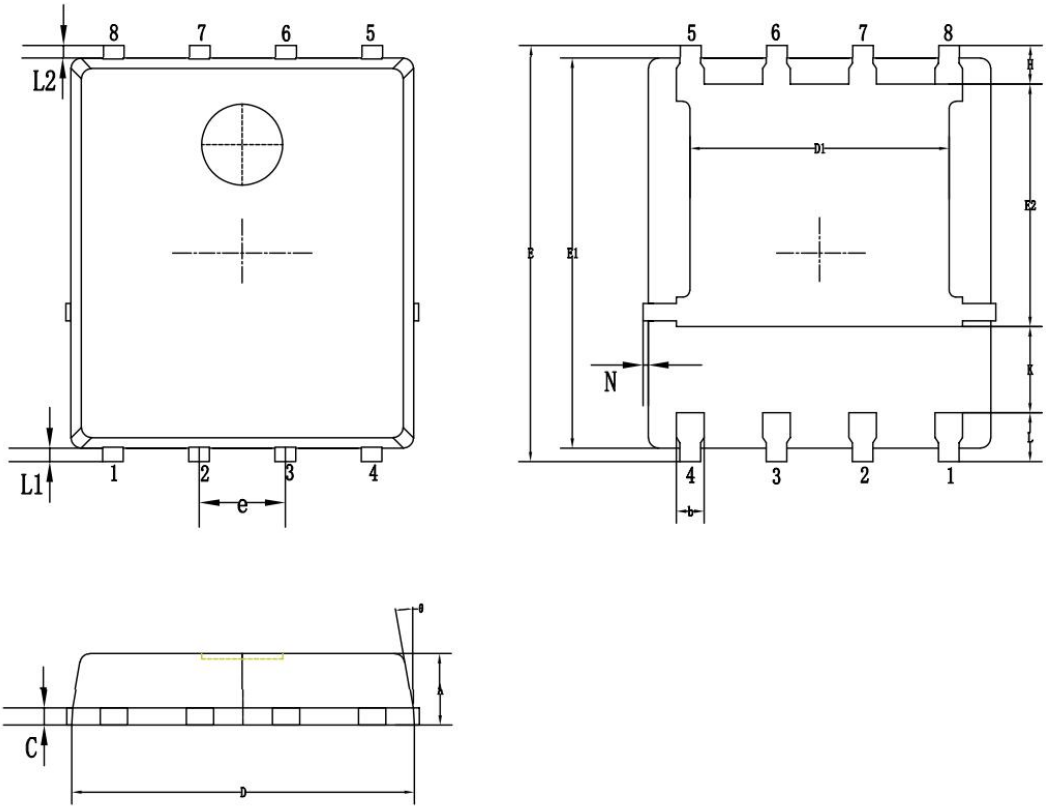



**Figure 9. Normalized Maximum Transient Thermal Impedance**



## PDFN5X6 Package Information




| Symbols | Millimeters | | |
|---|---|---|---|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.05 | 1.20 |
| b | 0.35 | 0.40 | 0.50 |
| C | 0.20 | 0.25 | 0.35 |
| D | 4.80 | 5.05 | 5.20 |
| D1 | 3.80 | 3.90 | 4.10 |
| E | 5.90 | 6.00 | 6.20 |
| E1 | 5.60 | 5.75 | 5.90 |
| E2 | 3.40 | 3.50 | 3.60 |
| e | 1.27 BSC. | | |
| H | 0.40 | 0.60 | 0.70 |
| K | 1.17 | 1.27 | 1.37 |
| L | 0.50 | 0.74 | 0.84 |
| L1/L2 | 0.10 | 0.16 | 0.20 |
| θ | 8° | 10° | 12° |
| N | 0 | - | 0.15 |

## Revision History

| Revision | Release | Remark |
|---|---|---|
| V1.0 | 2024/07/16 | Initial Release |

## Disclaimer

The information given in this document describes the independent performance of the product,but similar performance is not guaranteed under other working conditions,and cannot be guaranteed when installed with other products or equipment.To achieve the required performance of the product in actual scenarios,the customer should conduct a complete application test to assess the functionality of the product.

Allpower assumes no responsibility for equipment failures result from using products at values that exceed the ratings,operating conditions,or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which
requires high reliability.Customers using or selling these products for use in medical,life-saving,or life-sustaining applications do so at their own risk and agree to fully indemnify.

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